General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

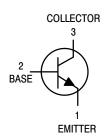
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

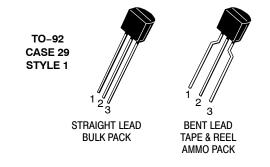
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



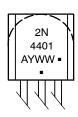
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MARKING DIAGRAM



2N4401 = Device Code A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	•	•
Collector – Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)		V _{(BR)CEO}	40	-	Vdc	
Collector-Base Breakdown	Voltage	$(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V _{(BR)CBO}	60	-	Vdc
Emitter-Base Breakdown V	oltage	(I _E = 0.1 mAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current		(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{BEV}	-	0.1	μAdc
Collector Cutoff Current		(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{CEX}	-	0.1	μAdc
ON CHARACTERISTICS (N	lote 1)					
DC Current Gain		$ \begin{array}{l} (I_{C}=0.1 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=500 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \end{array} $	h _{FE}	20 40 80 100 40	- - 300 -	-
Collector - Emitter Saturation	n Voltage	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{CE(sat)}	- -	0.4 0.75	Vdc
Base - Emitter Saturation Vo	ltage	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{BE(sat)}	0.75 -	0.95 1.2	Vdc
SMALL-SIGNAL CHARAC	TERISTICS					
Current-Gain - Bandwidth	Product (I	C = 20 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	250	_	MHz
Collector-Base Capacitance)	(V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	-	6.5	pF
Emitter-Base Capacitance		(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{eb}	-	30	pF
Input Impedance	(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	1.0	15	kΩ
Voltage Feedback Ratio	($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain	(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	40	500	-
Output Admittance	(I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	1.0	30	μmhos
SWITCHING CHARACTER	ISTICS					
Delay Time (V _{CC} = 30 Vdc, V _{BE} = 2.0 Vdc,		t _d	_	15	ns	
Rise Time	lise Time $I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$		t _r	-	20	ns
Storage Time	(V _{CC} = 30 Vdc, I	C = 150 mAdc,	t _s	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ m/}$	Adc)	t _f	_	30	ns

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N4401	TO-92	5000 Units / Bulk
2N4401G	TO-92 (Pb-Free)	5000 Units / Bulk
2N4401RLRA	TO-92	2000 / Tape & Reel
2N4401RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N4401RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
2N4401RLRP	TO-92	2000 / Tape & Ammo Box
2N4401RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

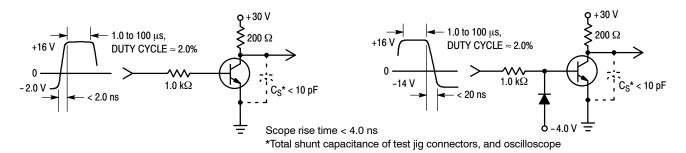


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

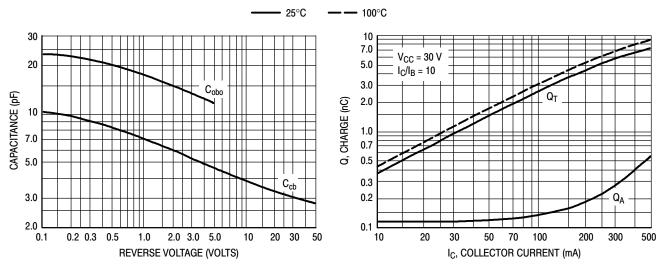


Figure 3. Capacitances

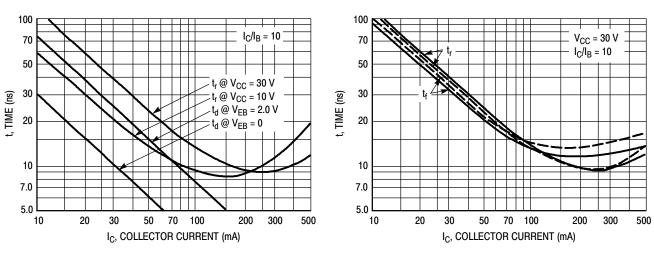
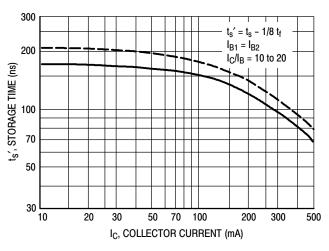


Figure 5. Turn-On Time

Figure 6. Rise and Fall Times

Figure 4. Charge Data



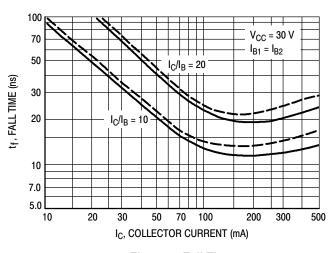
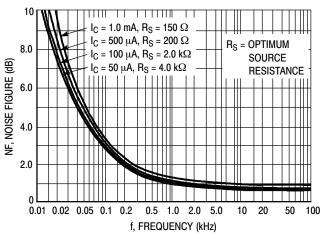


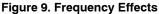
Figure 7. Storage Time

Figure 8. Fall Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz





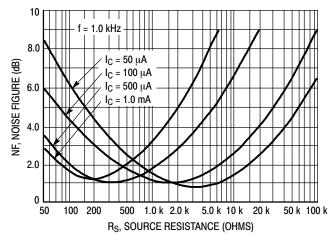


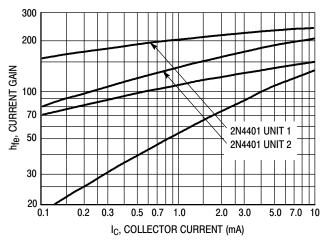
Figure 10. Source Resistance Effects

h PARAMETERS

 V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were

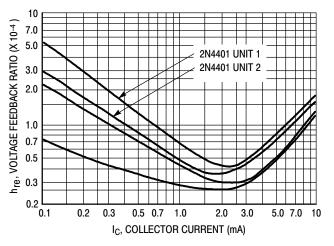
selected from the 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.



50 k 2N4401 UNIT 1 2N4401 UNIT 2 h_{ie}, INPUT IMPEDANCE (OHMS) 20 k 10 k 5.0 k 2.0 k 1.0 k 500 0.2 0.5 0.7 1.0 2.0 7.0 10 IC, COLLECTOR CURRENT (mA)

Figure 11. Current Gain

Figure 12. Input Impedance



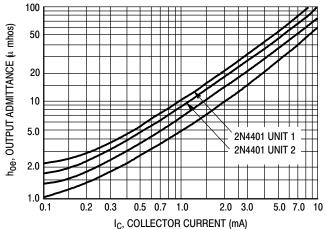


Figure 13. Voltage Feedback Ratio

Figure 14. Output Admittance

STATIC CHARACTERISTICS

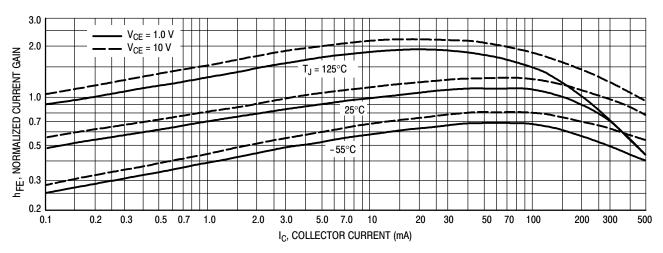


Figure 15. DC Current Gain

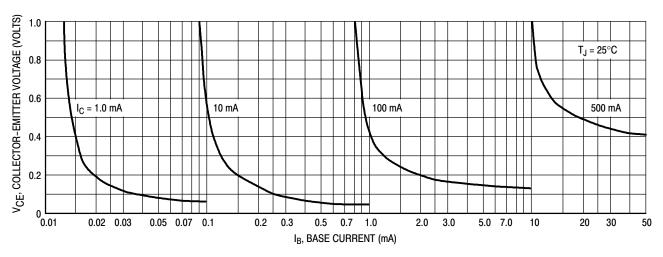


Figure 16. Collector Saturation Region

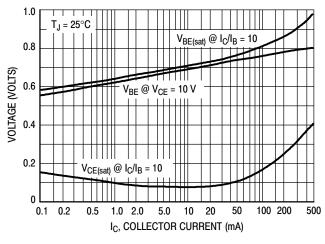


Figure 17. "On" Voltages

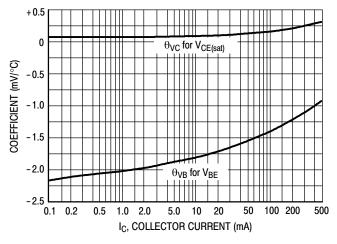
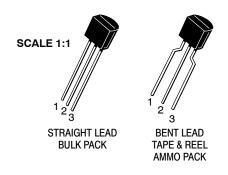
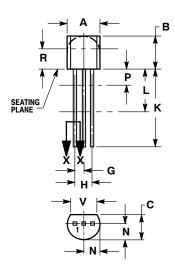


Figure 18. Temperature Coefficients



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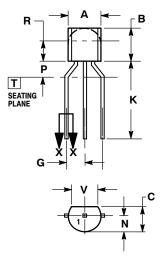


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS				
DIM	MIN	MAX			
Α	4.45	5.20			
В	4.32	5.33			
С	3.18	4.19			
D	0.40	0.54			
G	2.40	2.80			
J	0.39	0.50			
K	12.70				
N	2.04	2.66			
P	1.50	4.00			
R	2.93				
V	3.43				

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE
2.	ANODE CATHODE & ANODE CATHODE	2.	GATE	2.	ANODE 1 GATE CATHODE 2	2.	COLLECTOR	2.	CATHODE
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
PIN 1. 2.	COLLECTOR EMITTER BASE	PIN 1. 2. 3.	SOURCE GATE DRAIN	PIN 1. 2. 3.	GATE SOURCE DRAIN	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	2.	CATHODE ANODE GATE	PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	DRAIN
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	PIN 1. 2.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC	PIN 1. 2.	GATE

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